

PRELIMINARY

Notice : This is not a final specification
Some parametric limits are subject to change.

MITSUBISHI SEMICONDUCTOR <GaAs MMIC>

MGFC5216

Q-Band 4-Stage Driver Amplifier

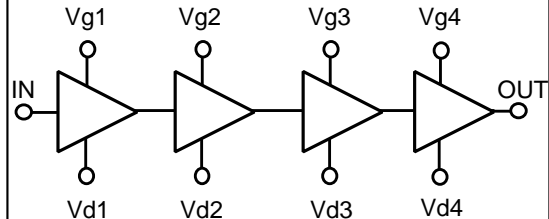
DESCRIPTION

The MGFC5216 is a GaAs MMIC chip especially designed for 37.0 ~ 40.0 GHz band Middle Power Amplifier (MPA) .

FEATURES

- RF frequency : 37.0 to 43.0 GHz
- Linear gain : 20dB (TYP.) @ 37 to 40 GHz
20 dB(TYP.) @ 40 to 43 GHz
- P1dB : 16 dBm(min.) @ 37 to 40 GHz
16 dBm(target) @ 40 to 43 GHz

BLOCK DIAGRAM



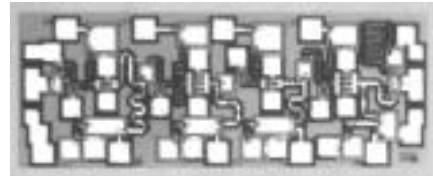
TARGET SPECIFICATIONS (Ta=25°C)

Parameter	Min.	Typical	Max.	Unit
Frequency	37	—	40	GHz
Linear Gain	—	20	—	dB
P1dB	16	—	—	dBm
Input VSWR	—	—	2.2	—
Output VSWR	—	—	2.0	—
Vd	Vd12=4.5, Vd34=6			V
Vg	-0.3			V
Chip Size	1.99x0.83			mm ²

Specification	Min.	Typical	Max.	Unit
Frequency	40	—	43	GHz
Linear Gain	—	20	—	dB
P1dB	(16)	—	—	dBm
Input VSWR	—	—	2.4	—
Output VSWR	—	—	3.0	—
Vd	Vd12=4.5, Vd34=6			V
Vg	-0.3			V
Chip Size	1.99x0.83			mm ²

():Design Target (Now Evaluating)

PHOTOGRAPH



PRELIMINARY

Notice : This is not a final specification
Some parametric limits are subject to change.

MITSUBISHI SEMICONDUCTOR <GaAs MMIC>

MGFC5216

Q-Band 4-Stage Driver Amplifier

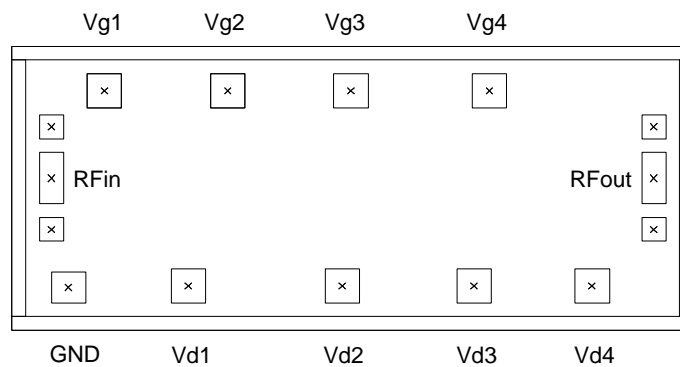
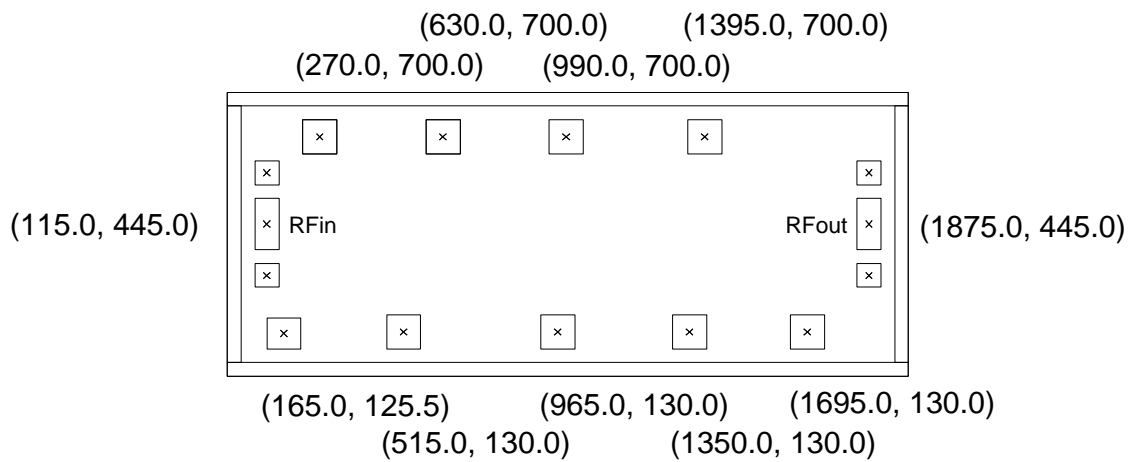
DIE SIZE AND BOND PAD LOCATION(UNIT : μM)

X=1.99 mm

Y=0.83 mm

Bond Pad Dimension=0.07 x 0.15 mm² (RF)

0.1 x 0.1 mm² (DC)



PRELIMINARY

Notice : This is not a final specification
Some parametric limits are subject to change.

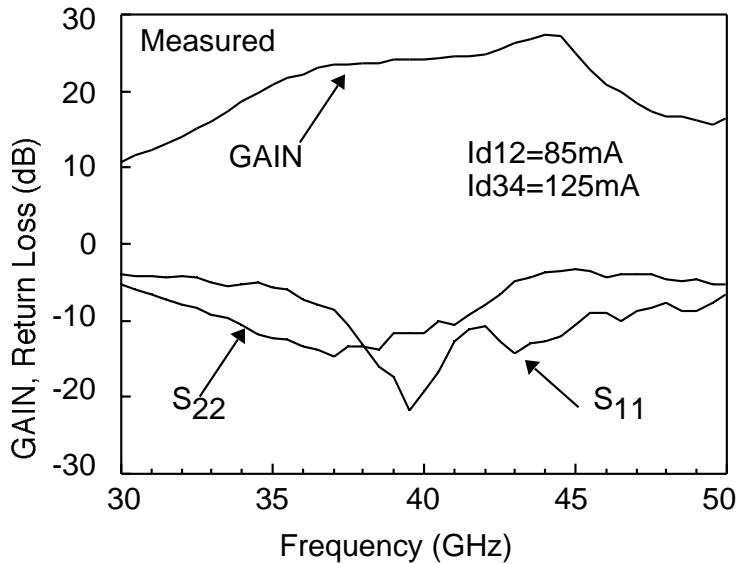
MITSUBISHI SEMICONDUCTOR <GaAs MMIC>

MGFC5216

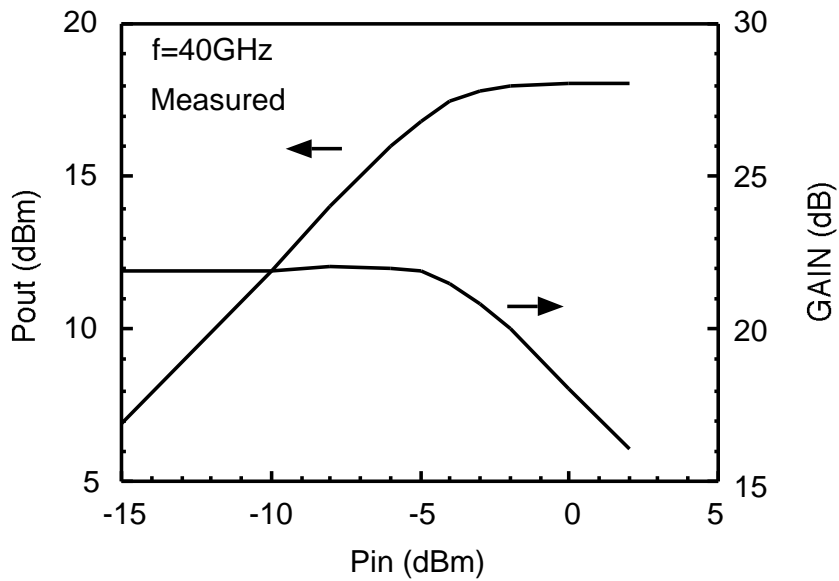
Q-Band 4-Stage Driver Amplifier

TYPICAL CHARACTERISTICS

S-Parameter vs. Frequency



Output Power Performances



PRELIMINARY

Notice : This is not a final specification
Some parametric limits are subject to change.

MITSUBISHI SEMICONDUCTOR <GaAs MMIC>

MGFC5216

Q-Band 4-Stage Driver Amplifier

AN EXAMPLE OF TEST CIRCUIT

